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30 V, 180 mA N-channel Trench MOSFET 29 October 2013

Product data sheet

1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a small SOT323 (SC-70) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- Very fast switching
- Trench MOSFET technology
- ESD protection
- Low threshold voltage

3. Applications

- Relay driver
- High-speed line driver
- Low-side loadswitch
- Switching circuits

4. Quick reference data

Table 1. Quie	ck reference data							
Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
V _{DS}	drain-source voltage	T _j = 25 °C		-	-	30	V	
V _{GS}	gate-source voltage			-20	-	20	V	
I _D	drain current	V _{GS} = 10 V; T _{amb} = 25 °C	[1]	-	-	180	mA	
Static characteristics								
R _{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I _D = 100 mA; T _j = 25 °C		-	2.7	4.5	Ω	

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².





30 V, 180 mA N-channel Trench MOSFET

5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	3	D
2	S	source		
3	D	drain	1 ☐ ☐ 2 SC-70 (SOT323)	G S 017aaa255

6. Ordering information

Table 3. Ordering information							
Type number	Package						
	Name	Description	Version				
NX3020NAKW	SC-70	plastic surface-mounted package; 3 leads	SOT323				

7. Marking

Table 4. Marking codes	
Type number	Marking code
	[1]
NX3020NAKW	%3A

[1] % = placeholder for manufacturing site code

8. Limiting values

Table 5.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Мах	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	30	V
V _{GS}	gate-source voltage			-20	20	V
I _D	drain current	V _{GS} = 10 V; T _{amb} = 25 °C	[1]	-	180	mA
		V _{GS} = 10 V; T _{amb} = 100 °C	[1]	-	110	mA
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10 \ \mu s$		-	720	mA
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	260	mW
			[1]	-	300	mW

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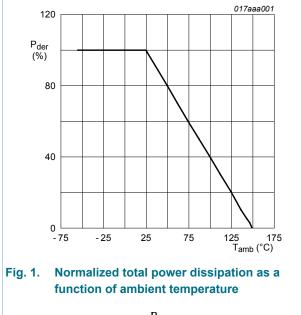
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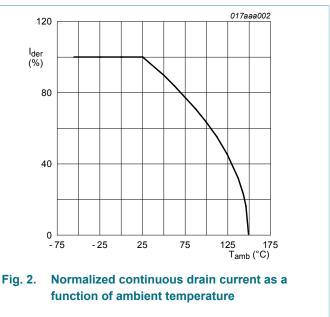
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Symbol	Parameter	Conditions		Min	Мах	Unit	
		T _{sp} = 25 °C		-	1100	mW	
Tj	junction temperature			-55	150	°C	
T _{amb}	ambient temperature			-55	150	°C	
T _{stg}	storage temperature			-65	150	°C	
Source-drain diode							
I _S	source current	T _{amb} = 25 °C	[1]	-	180	mA	

Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².
 Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

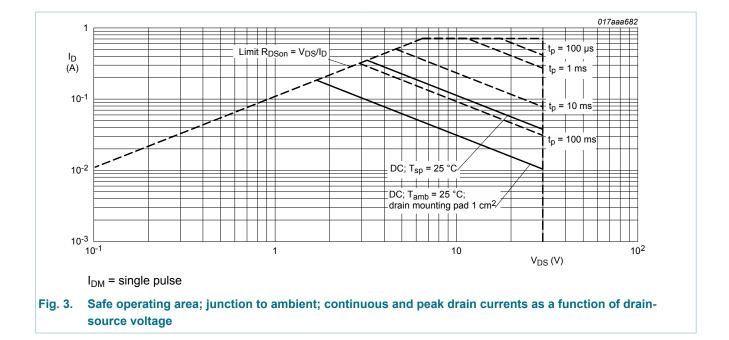


$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$



$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100 \%$$

30 V, 180 mA N-channel Trench MOSFET



9. Thermal characteristics

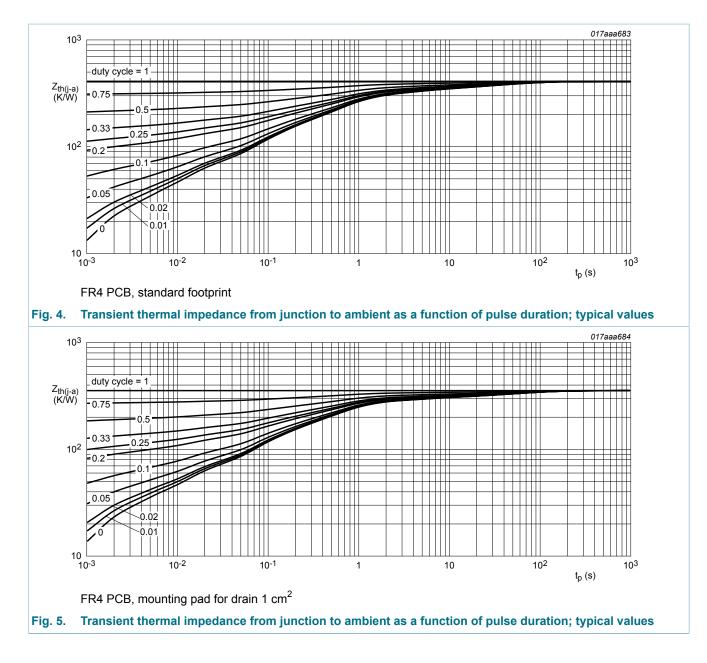
Table 6. Thermal characteristics								
Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	[1]	-	415	480	K/W	
			[2]	-	350	400	K/W	
R _{th(j-sp)}	thermal resistance from junction to solder point			-	-	110	K/W	

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².

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30 V, 180 mA N-channel Trench MOSFET



10. Characteristics

Table 7. Cl	haracteristics							
Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
Static characteristics								
V _{(BR)DSS}	drain-source breakdown voltage	I_D = 250 µA; V_{GS} = 0 V; T_j = 25 °C		30	-	-	V	
V _{GSth}	gate-source threshold voltage	I _D = 250 μA; V _{DS} = V _{GS} ; T _j = 25 °C		0.8	1.2	1.5	V	
I _{DSS}	drain leakage current	V_{DS} = 30 V; V_{GS} = 0 V; T_j = 25 °C		-	-	1	μA	
		V_{DS} = 30 V; V_{GS} = 0 V; T_j = 150 °C		-	-	10	μA	
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Product data sheet

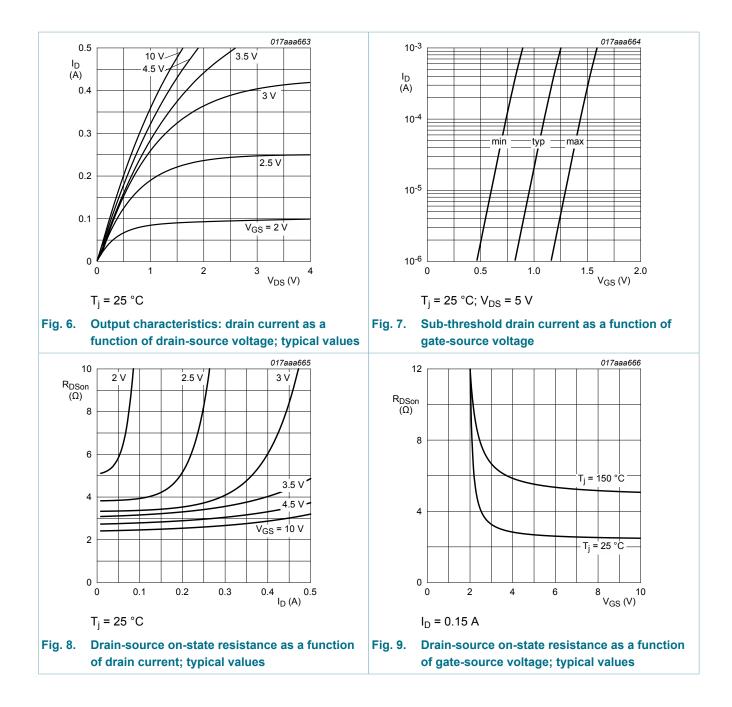
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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{GSS}	gate leakage current	V_{GS} = 20 V; V_{DS} = 0 V; T_j = 25 °C	-	-	3.5	μA
		V_{GS} = -20 V; V_{DS} = 0 V; T_j = 25 °C	-	-	3.5	μA
		V_{GS} = 10 V; V_{DS} = 0 V; T_j = 25 °C	-	-	1	μA
		V_{GS} = -10 V; V_{DS} = 0 V; T_j = 25 °C	-	-	1	μA
		V_{GS} = 4.5 V; V_{DS} = 0 V; T_j = 25 °C	-	-	0.5	μA
		V_{GS} = -4.5 V; V_{DS} = 0 V; T_j = 25 °C	-	-	0.5	μA
R _{DSon}	drain-source on-state	V_{GS} = 10 V; I _D = 100 mA; T _j = 25 °C	-	2.7	4.5	Ω
	resistance	V_{GS} = 10 V; I _D = 100 mA; T _j = 150 °C	-	5.5	9.2	Ω
		V_{GS} = 4.5 V; I _D = 100 mA; T _j = 25 °C	-	3	5.2	Ω
		V _{GS} = 2.5 V; I _D = 10 mA; T _j = 25 °C	-	4	13	Ω
9fs	forward transconductance	V _{DS} = 10 V; I _D = 150 mA; T _j = 25 °C	-	320	-	S
Dynamic cl	haracteristics	· · · · · ·				
Q _{G(tot)}	total gate charge	V _{DS} = 15 V; I _D = 150 mA; V _{GS} = 4.5 V;	-	0.34	0.44	nC
Q _{GS}	gate-source charge	T _j = 25 °C	-	0.11	-	nC
Q _{GD}	gate-drain charge		-	0.06	-	nC
C _{iss}	input capacitance	V _{DS} = 10 V; f = 1 MHz; V _{GS} = 0 V;	-	13	20	pF
C _{oss}	output capacitance	T _j = 25 °C	-	2.6	-	pF
C _{rss}	reverse transfer capacitance		-	1.1	-	pF
t _{d(on)}	turn-on delay time	V_{DS} = 20 V; R _L = 250 Ω; V _{GS} = 10 V;	-	5	10	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	5	-	ns
t _{d(off)}	turn-off delay time		-	34	68	ns
t _f	fall time		-	17	-	ns
Source-dra	in diode	· · ·	1			
V _{SD}	source-drain voltage	I _S = 115 mA; V _{GS} = 0 V; T _j = 25 °C	0.47	0.7	1.2	V

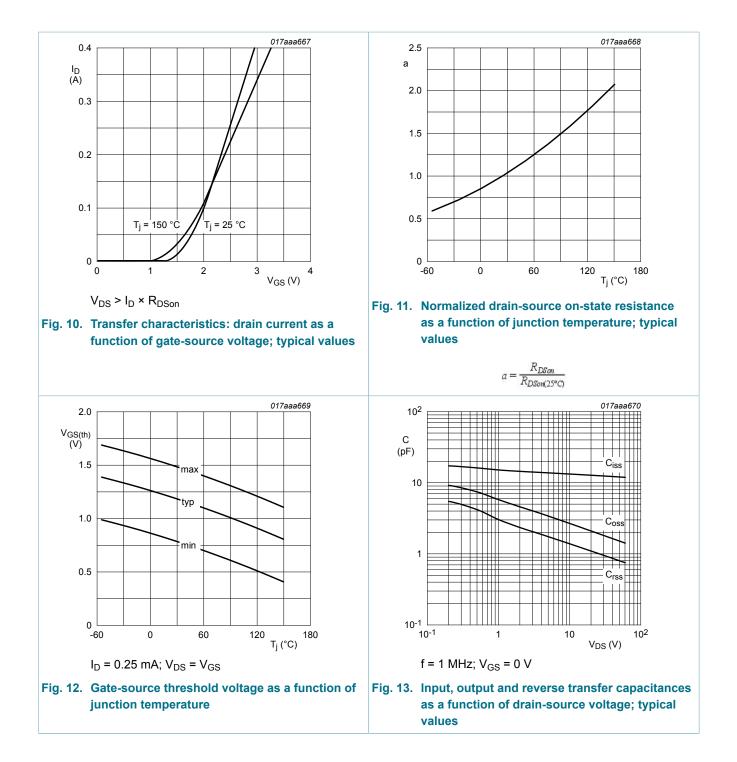
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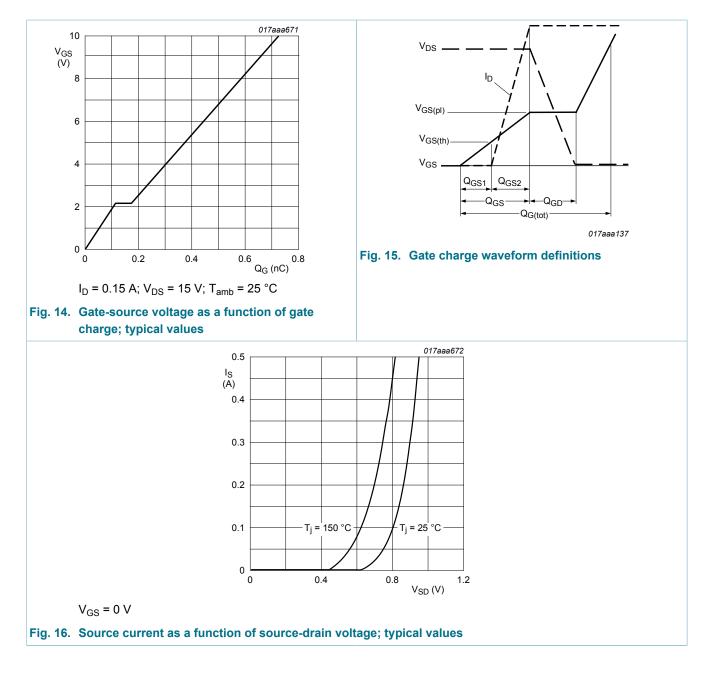
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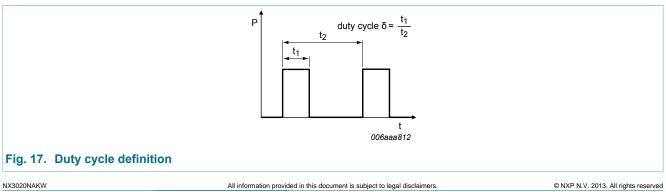


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11. Test information



30 V, 180 mA N-channel Trench MOSFET

12. Package outline

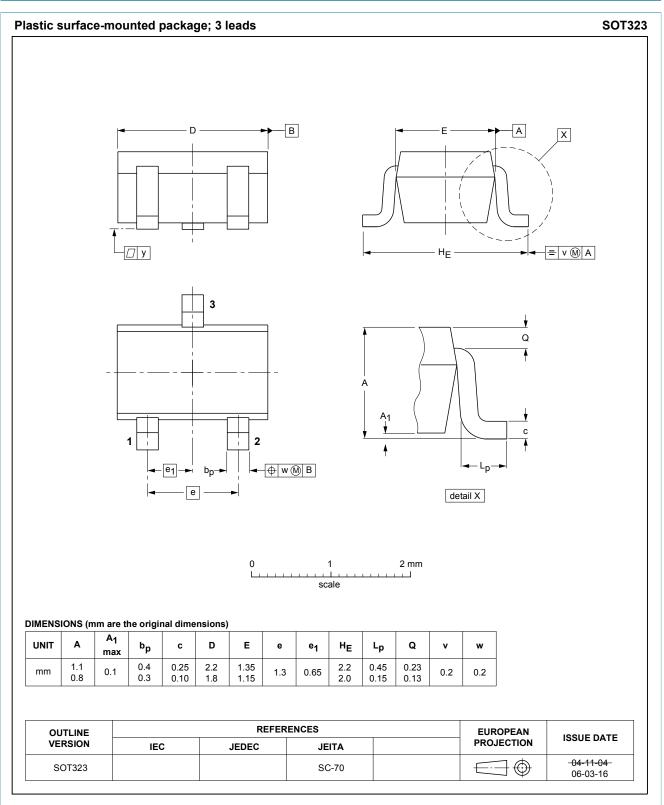


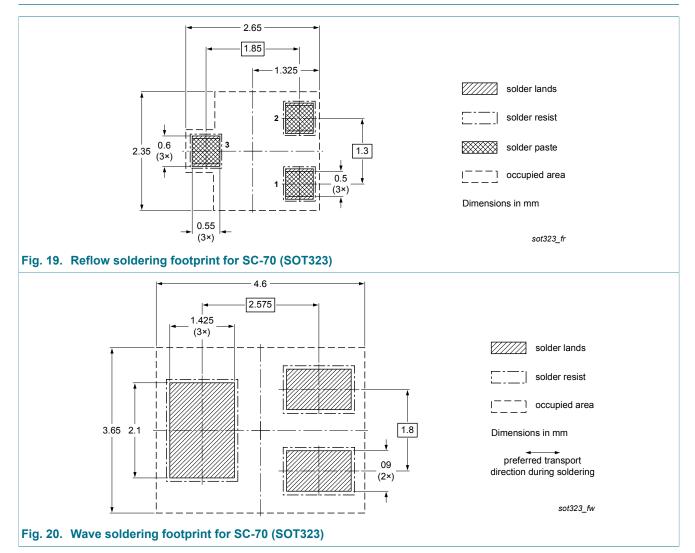
Fig. 18. Package outline SC-70 (SOT323)

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30 V, 180 mA N-channel Trench MOSFET

13. Soldering



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14. Revision history

Table 8. Revision history								
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes				
NX3020NAKW v.2	20131029	Product data sheet	-	NX3020NAKW v.1				
Modifications:	 3D package outline added Table 7 values of capacitance parameters corrected Figure 13 corrected 							
NX3020NAKW v.1	20120830	Product data sheet	-	-				

30 V, 180 mA N-channel Trench MOSFET

15. Legal information

15.1 Data sheet status

Document status [1][2]	Product status [<u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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